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U.S. PATENT DOCUMENTS									
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				POREIGN PATENT DOCUMENTS				 	
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INITIAL							YES	NO	
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1		Todd, Michael A. et al., "Deposition of Si 1-x Ge x Films for Gate Electrode Applications Using a Novel Approach," ICSI3, The SiGe Conference; Santa Fe, NM, March 2003							
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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

APPI APPI

APPLICANT Michael A. Todd

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February 11, 2002

GROUP 2814

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7		2.	5,698,771	12/16/97	Shields et al.	73	31.05	
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	7. Ikoma et al., Growth of Si/3C-SiC/Si(100) hetrostructures by pulsed supersonic free jets, Applied Physics Letters, Volume 75, No. 25, Pp. 3977-3979, December 1999

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